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September 2013

FGP10N60UNDF 600 V, 10 A Short Circuit Rated IGBT

Features

- · Short Circuit Rated 10 us
- High Current Capability
- High Input Impedance
- · Fast Switching
- RoHS Compliant

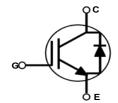
General Description

Using advanced NPT IGBT technology, Fairchild's the NPT IGBTs offer the optimum performance for low-power inverterdriven applications where low-losses and short-circuit ruggedness features are essential, such as sewing machine, CNC, motor control and home appliances.

Applications

· Sewing Machine, CNC, Home Appliances, Motor Control





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit
V _{CES}	Collector to Emitter Voltage		600	V
V_{GES}	Gate to Emitter Voltage		± 20	V
Ic	Collector Current	@ T _C = 25°C	20	A
'C	Collector Current	@ T _C = 100°C	10	Α
I _{CM (1)}	Pulsed Collector Current	@ T _C = 25°C	30	A
l _F	Diode Forward Current	@ $T_C = 25^{\circ}C$	10	Α
	Diode Forward Current	@ T _C = 100°C	5	Α
PD	Maximum Power Dissipation	@ TC = 25oC	139	W
. 5	Maximum Power Dissipation	@ TC = 100oC	56	W
TJ	Operating Junction Temperature		-55 to +150	°C
T _{stg}	Storage Temperature Range		-55 to +150	°C

Notes

Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case	-	0.9	°C/W
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction to Case	-	3.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (PCB Mount)(2)	-	62.5	°C/W

Notes

2: Mountde on 1" square PCB (FR4 or G-10 material)

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGP10N60UNDF	FGP10N60UNDF	TO-220	-	-	50ea

Electrical Characteristics of the IGBT $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	eteristics					
BV _{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_{C} = 250 \mu\text{A}$	600	-	-	V
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0 V$	-	-	1	mA
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$	-	-	±10	uA
On Charac	teristics					
V _{GE(th)}	G-E Threshold Voltage	$I_C = 10 \text{ mA}, V_{CE} = V_{GE}$	5.5	6.8	8.5	V
		I _C = 10 A, V _{GE} = 15 V	-	2	2.45	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 10 A, V _{GE} = 15 V, T _C = 125°C	-	2.3	-	V
Dynamic C	Characteristics			•		
C _{ies}	Input Capacitance		-	517		pF
C _{oes}	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1 MHz	-	65		pF
C _{res}	Reverse Transfer Capacitance	1 = 1 10102	-	20		pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time		-	8.0		ns
t _r	Rise Time		-	6.3		ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 400 \text{ V}, I_{C} = 10 \text{ A},$	-	52.2		ns
t _f	Fall Time	$R_G = 10 \Omega$, $V_{GE} = 15 V$,	-	19.1	24.8	ns
E _{on}	Turn-On Switching Loss	Inductive Load, $T_C = 25^{\circ}C$	-	0.15		mJ
E _{off}	Turn-Off Switching Loss		-	0.05		mJ
E _{ts}	Total Switching Loss		-	0.2		mJ
t _{d(on)}	Turn-On Delay Time		-	8.1		ns
t _r	Rise Time		- /	7.3		ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 400 \text{ V}, I_{C} = 10 \text{ A},$	-	55.1	,	ns
t _f	Fall Time	$R_G = 10 \Omega$, $V_{GE} = 15 V$,	-	34.2		ns
E _{on}	Turn-On Switching Loss	Inductive Load, $T_C = 125^{\circ}C$	-	0.22		mJ
E _{off}	Turn-Off Switching Loss		-	0.08		mJ
E _{ts}	Total Switching Loss		-	0.3		mJ
T _{sc}	Short Circuit Withstand Time	$V_{CC} = 350 \text{ V},$ $R_G = 100 \Omega, V_{GE} = 15 \text{V},$ $T_C = 150^{\circ}\text{C}$	10	-	- (μs

Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max	Unit
Qg	Total Gate Charge		-	37		nC
Q _{ge}	Gate to Emitter Charge	$V_{CE} = 400 \text{ V}, I_{C} = 10 \text{ A},$ $V_{GE} = 1 \text{ V}$	-	5		nC
Q _{gc}	Gate to Collector Charge	VGE - I V	-	21		nC

Electrical Characteristics of the Diode $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter		Test Conditions		Min.	Тур.	Max	Unit	
V _{FM}	Diode Forward Voltage	I _F =	10 A		$T_C = 25^{\circ}C$	-	1.8	2.2	V
V FM					$T_{\rm C} = 125^{\rm o}{\rm C}$	-	1.7		
t _{rr}	Diode Reverse Recovery Time		= 10 A, dI _F /dt = 200 A/μs		$T_C = 25^{\circ}C$	-	37.7		ns
11	Blode Neverse Nessevery Time				$T_{\rm C} = 125^{\rm o}{\rm C}$	1	78.9		
Q _{rr}	Diode Reverse Recovery Charge				$T_C = 25^{\circ}C$	-	75		nC
~rr					$T_{\rm C} = 125^{\rm o}{\rm C}$	-	221		

TTypical Performance Characteristics

Figure 1. Typical Output Characteristics

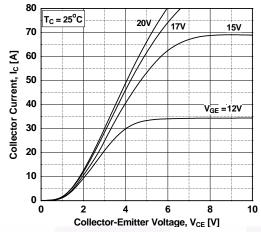


Figure 3. Typical Saturation Voltage Characteristics

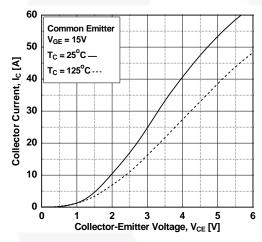


Figure 5. Saturation Voltage vs. Case

Temperature at Variant Current Level

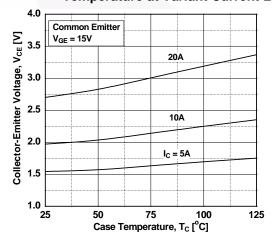


Figure 2. Typical Output Characteristics

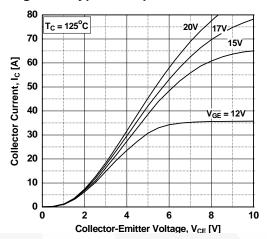


Figure 4. Transfer Characteristics

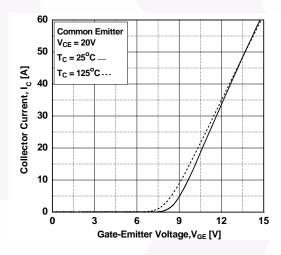
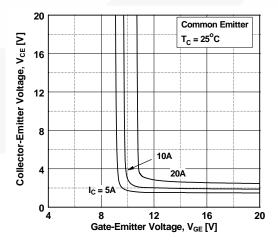


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics

Figure 7. Saturation Voltage vs. V_{GE}

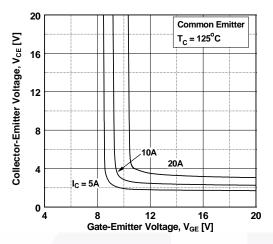


Figure 9. Gate charge Characteristics

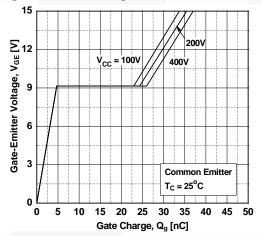


Figure 11. Turn-on Characteristics vs.
Gate Resistance

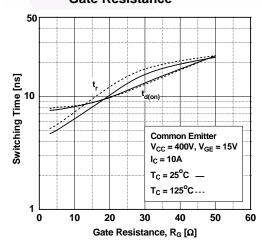


Figure 8. Capacitance Characteristics

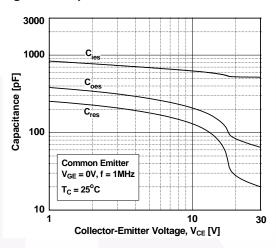


Figure 10. SOA Characteristics

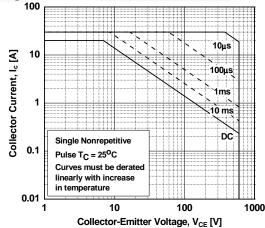
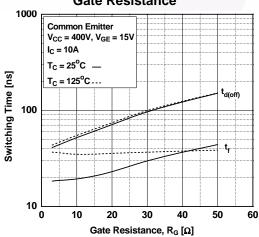


Figure 12. Turn-off Characteristics vs. Gate Resistance



Typical Performance Characteristics

Figure 13. Turn-on Characteristics vs. Collector Current

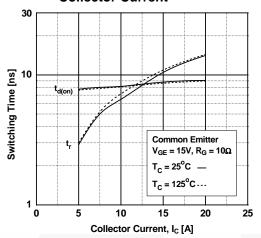


Figure 15. Switching Loss vs.

Gate Resistance

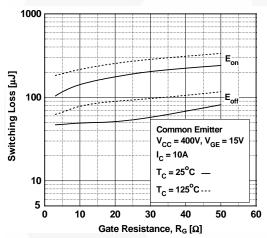


Figure 17. Turn off Switching SOA Characteristics

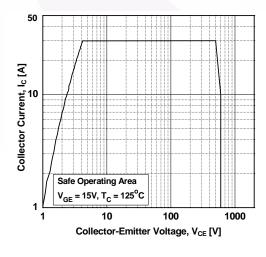


Figure 14. Turn-off Characteristics vs.
Collector Current

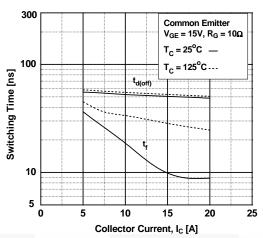


Figure 16. Switching Loss vs Collector Current

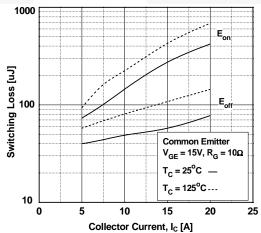
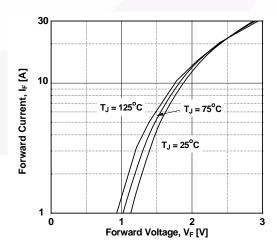


Figure 18. Forward Characteristics



Typical Performance Characteristics

Figure 19. Reverse Recovery Current

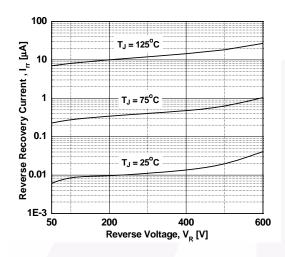


Figure 20. Stored Charge

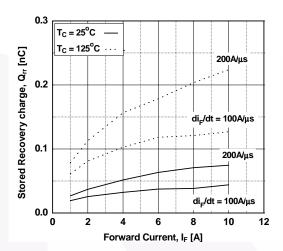


Figure 21. Reverse Recovery Time

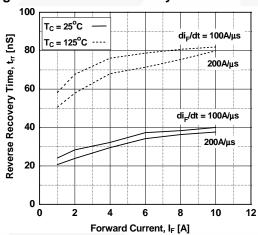
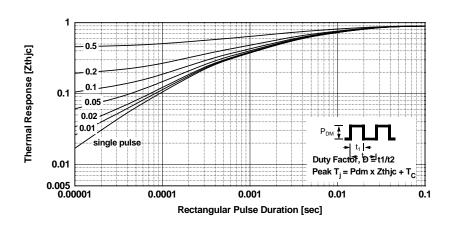


Figure 22. Transient Thermal Impedance of IGBT



Mechanical Dimensions

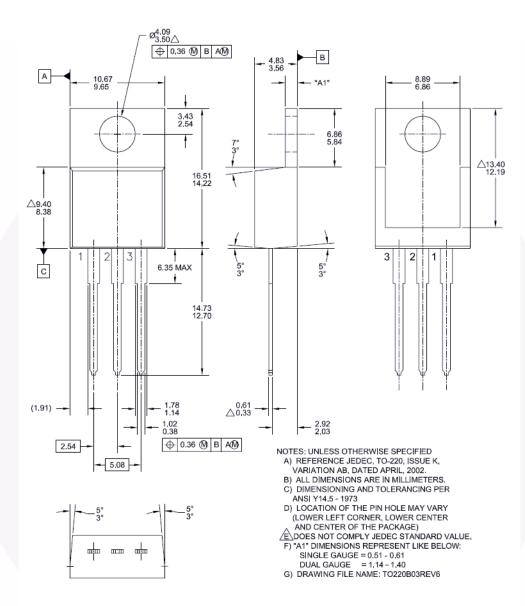


Figure 23. TO-220 3L - TO-220, MOLDED, 3LEAD, JEDEC VARIATION AB

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Dimensions in Millimeters





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